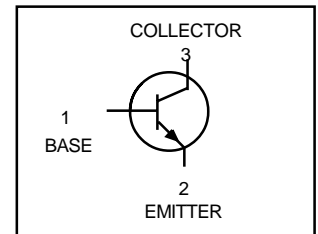
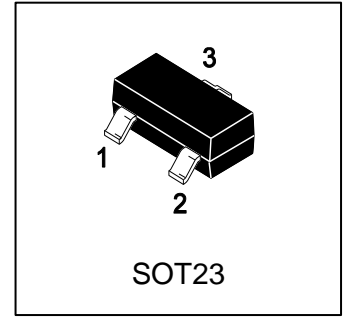


# LH8050QLT1G

## S-LH8050QLT1G

General Purpose Transistors NPN Silicon



### 1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- High current capacity in compact package.  
IC =1.5A.
- Epitaxial planar type.
- Pb-Free Package is available.

### 2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LH8050QLT1G	KEY	3000/Tape&Reel
LH8050QLT3G	KEY	10000/Tape&Reel

### 3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-Emitter Voltage	VCEO	50	V
Collector-Base voltage	VCBO	50	V
Emitter-Base Voltage	VEBO	6	V
Collector current	IC	1500	mA

### 4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation FR-5 Board(Note 1) TA =25°C	PD	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance,Junction to Ambient	RθJA	556	°C/W
Thermal Resistance,Junction to Case	RθJC	300	
Junction and Storage temperature	TJ,Tstg	-55~+150	°C

1. FR-5 = 1.0 x 0.75 x 0.062 in.

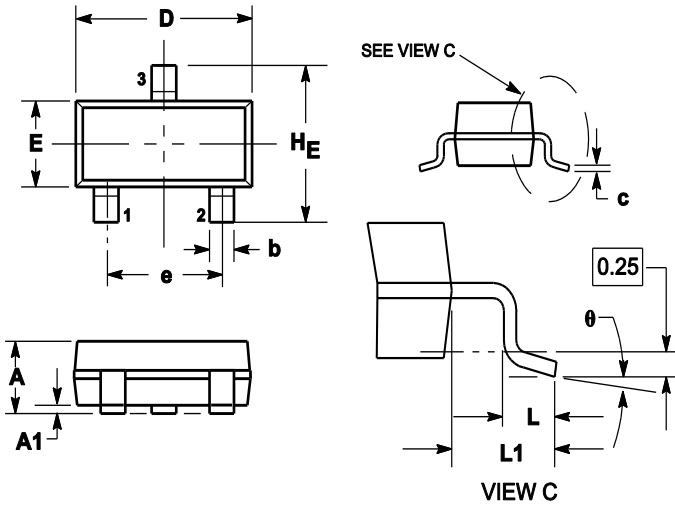
**5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)**

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector-Emitter Breakdown Voltage (IC =2.0mA,IB =0)	V(BR)CEO	50	-	-	V
Emitter-Base Breakdown Voltage (IE = 100μA,IC=0)	V(BR)EBO	6	-	-	V
Collector-Base Breakdown voltage (IC = 100μA,IE=0)	V(BR)CBO	50	-	-	V
Collector Cutoff Current (VCB = 35 V,IE=0)	ICBO	-	-	100	nA
Emitter Cutoff Current (VEB = 6V,IC=0)	IEBO	-	-	100	nA
Base-Emitter Voltage (VCE =1V,IC =10mA)	VBE	-	0.66	1	V
DC Current Gain (IC =100mA, VCE =1V) (IC=800mA, VCE =1V)	HFE	160 40	- -	320 -	
Collector-Emitter Saturation Voltage (IC =800mA, IB =80mA)	VCE(S)	-	-	0.5	V
Base-Emitter Saturation Voltage (IC =800mA, IB =80mA)	VBE(S)	-	-	1.2	V

### 6. OUTLINE AND DIMENSIONS

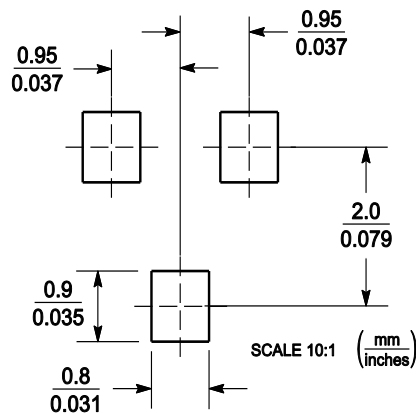
Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1	1.11	0.035	0.04	0.044
A1	0.01	0.06	0.1	0.001	0.002	0.004
b	0.37	0.44	0.5	0.015	0.018	0.02
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.9	3.04	0.11	0.114	0.12
E	1.20	1.3	1.4	0.047	0.051	0.055
e	1.78	1.9	2.04	0.07	0.075	0.081
L	0.10	0.2	0.3	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.4	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

### 7. SOLDERING FOOTPRINT



## **DISCLAIMER**

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
- Before you use our Products for new Project, you are requested to carefully read this document and fully understand its contents. LRC shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of any LRC's Products against warning, caution or note contained in this document.
- All information contained in this document is current as of the issuing date and subject to change without any prior notice. Before purchasing or using LRC's Products, please confirm the latest information with a LRC sales representative.

单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)